



Certificate TH97/10561QM

Certificate TW00/17276EM

BAX12, BAX12A

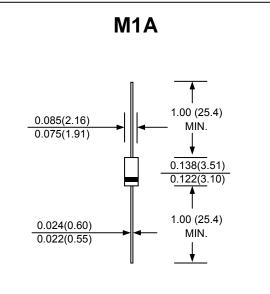
CONTROLLED AVALANCHE DIODES

FEATURES:

- * Switching speed: max. 50 ns
- * Continuous reverse voltage: max. 90V
- * Repetitive peak reverse voltage: max. 90V
- * Repetitive peak forward current: max.800 mA
- * Repetitive peak reverse current: max.600mA
- * Pb / RoHS Free

MECHANICAL DATA:

- * Case : M1A Molded plastic
- * Epoxy : UL94V-O rate flame retardant
- * Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
- * Polarity : Color band denotes cathode end
- * Mounting position : Any
- * Weight : 0.20 gram (approximately)



Dimensions in inches and (millimeters)

Maximum Ratings

Parameter		Symbol	Value	Unit
Repetitive Peak Reverse Voltage		V _{RRM}	90	V
Continuous Reverse Voltage		V _R	90	V
Continuous Forward Current		I _F	400	mA
Repetitive Peak Forward Current		I _{FRM}	800	Α
Non-repetitive Peak Forward Current	t = 1 µs		55	
Square wave: Tj = 25 °C prior to surge	t = 100 µs	I _{FSM}	15	Α
	t = 10 ms		9	
Total Power Dissipation , Ta = 25 °C		P _{tot}	450	mW
Repetitive Peak Reverse Current		I _{RRM}	600	mA
Junction Temperature		TJ	200	°C
Storage Temperature Range		Ts	-65 to + 200	°C

Note : (1) Device mounted on an FR4 printed circuit-board; lead length 10 mm.

Electrical Characteristics (T_J = 25°C unless otherwise noted)

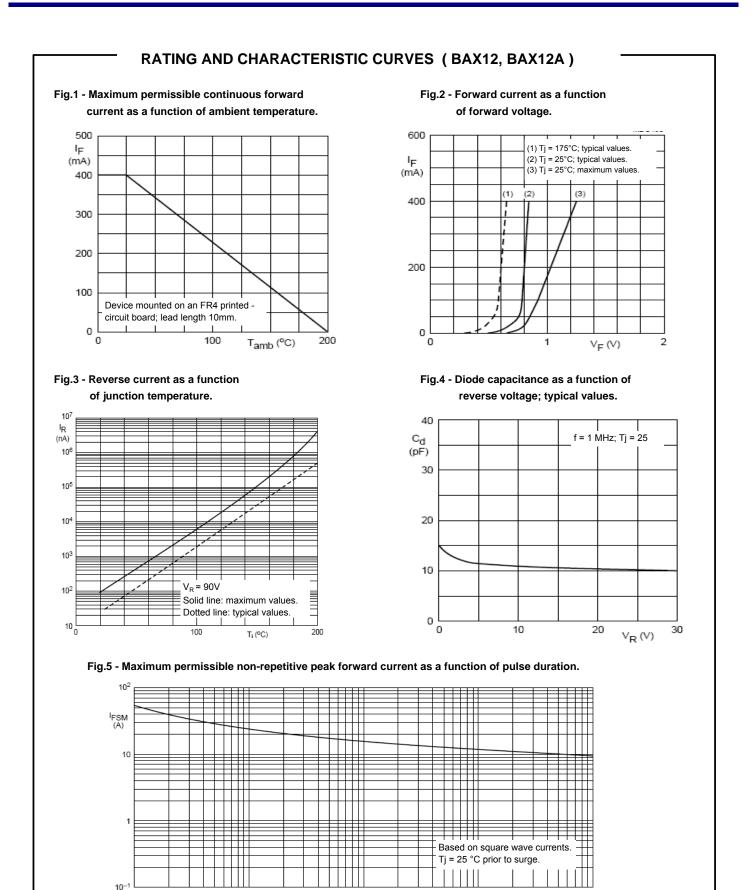
Parameter	Symbol	Test Condition	Min.	Max.	Unit
Reverse Avalanche BAX12	V _{(BR)R}	I _R = 1mA	120	170	V
Breakdown Voltage BAX12A	V (BR)R	I _R = 0.1mA	120	170	V
Reverse Current	I _R	V _R = 90 V	-	100	nA
		V _R = 90 V, Tj = 150 °C	-	100	μA
Forward Voltage	V _F	I _F = 400 mA	-	1.25	V
Diode Capacitance	Cd	f = 1MHz ; V _R = 0	-	35	pF
		I _F = 30mA , I _R = 30mA			
Reverse Recovery Time	Trr	$R_L = 100 \Omega$ measured at	-	50	ns
		I _R = 3 mA			





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 10^{2}

10

 10^{4}

t_D (μs)

103